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Chemistry, Pohang University of Science and Technology,
San 31 Hyoja-dong, Nam-gu, Pohang-city, Kyung-sang-
buk-do 790-784 (KR).

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(74) Agent: LEE, Young-Pil; The Cheonghwa Bldg., 1571-18
Seocho-dong, Seocho-gu, Seoul 137-874 (KR).

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(71) Applicant (for all designated States except US):
POSTECH FOUNDATION [KR/KR]; San 31 Hy-
oja-dong, Nam-gu, Pohang-city, Kyung-sang-buk-do
790-784 (KR).

(72) Inventors; and

(75) Inventors/Applicants (for US only): REE, Moonhor
[KR/KR]; Dept. of Chemistry, Pohang University of
Science and Technology, San 31 Hyoja-dong, Nam-gu,
Pohang-city, Kyung-sang-buk-do 790-784 (KR). OH,
Weontae [KR/KR]; Dept. of Chemistry, Pohang Uni-
versity of Science and Technology, San 31 Hyoja-dong,
Nam-gu, Pohang-city, Kyung-sang-buk-do 790-784 (KR).
HWANG, Yong-Taek [KR/KR]; Dept. of Chemistry,
Pohang University of Science and Technology, San 31
Hyoja-dong, Nam-gu, Pohang-city, Kyung-sang-buk-do
790-784 (KR). LEE, Byeongdu [KR/KR]; Dept. of

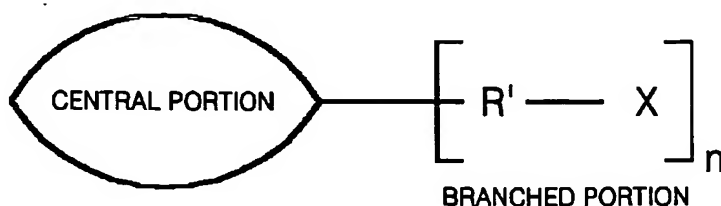
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(54) Title: LOW DIELECTRIC ORGANOSILICATE POLYMER COMPOSITE



(57) Abstract: Provided are a porous organosilicate polymer composite prepared by heating an organic/inorganic hybrid polymer in which an organosilicate polymer is chemically bonded to a radial pore-forming polymer ended with a hydrolyzable alkoxysilyl group and used as a core molecule, and a semiconductor device using an organosilicate polymer composite film including the porous organosilicate polymer composite. The organosilicate polymer

composite film has a very low dielectric constant, and thus, is useful as a dielectric film of the semiconductor device.

WO 2005/019303 A1